

# NTE2305 (NPN) & NTE2306 (PNP) Silicon Complementary Transistors High Voltage Power Amplifier TO-3PN Type Package

#### **Description:**

The NTE2305 (NPN) and NTE2306 (PNP) are silicon complementary transistors in a TO-3PN type package designed for use in high power audio amplifier applications and high voltage switching regulator circuits.

#### Features:

- High Collector-Emitter Sustaining Voltage: V<sub>CEO(sus)</sub> = 160V
- High DC Current Gain: h<sub>FE</sub> = 35 Typ @ I<sub>C</sub> = 8A
- Low Collector–Emitter Saturation Voltage: V<sub>CE(sat)</sub> = 2V Max @ I<sub>C</sub> = 8A

**Absolute Maximum Ratings:** 

### **Electrical Characteristics:** $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit				
OFF Characteristics										
Collector-Emitter Sustaining Voltage	V <sub>CEO(sus)</sub>	I <sub>C</sub> = 200mA, I <sub>B</sub> = 0, Note 2	160	_	-	V				
Collector-Emitter Cutoff Current	I <sub>CEX</sub>	V <sub>CE</sub> = 160V, V <sub>EB(off)</sub> = 1.5V	_	_	0.1	mA				
		$V_{CE} = 160V, V_{EB9off)} = 1.5V, T_{C} = +150^{\circ}C$	-	-	5.0	mA				
	I <sub>CEO</sub>	V <sub>CE</sub> = 80V, I <sub>B</sub> = 0	-	_	750	μА				
Emitter-Base Cutoff Current	I <sub>EBO</sub>	V <sub>BE</sub> = 7V, I <sub>C</sub> = 0	-	-	1.0	mA				
Collector-Base Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = 160V, I <sub>E</sub> = 0	_	_	750	μА				

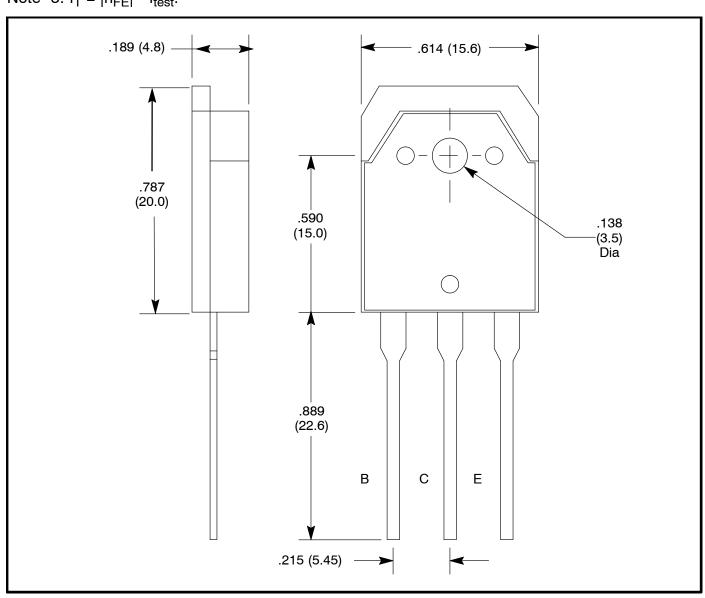
Note 2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≥ 2%.

## **Electrical Characteristics (Cont'd):** $(T_C = +25^{\circ}C \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit				
ON Characteristics (Note 2)										
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 8A	15	35	_					
		V <sub>CE</sub> = 4V, I <sub>C</sub> = 16A	8	15	_					
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 8A, I <sub>B</sub> = 0.8A	-	_	2.0	V				
		I <sub>C</sub> = 16A, I <sub>B</sub> = 2A	-	_	3.5	V				
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 16A, I <sub>B</sub> = 2A	-	_	3.9	V				
Base-Emitter ON Voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = 4V, I <sub>C</sub> = 16A	-	_	3.9	V				
Dynamic Characteristics										
Current-Gain Bandwidth Product	f <sub>T</sub>	$V_{CE} = 20V$ , $I_{C} = 1A$ , $f = 0.5MHz$ , Note 3	1.0	_	_	MHz				
Output Capacitance	C <sub>ob</sub>	$V_{CB} = 10V, I_E = 0, f = 0.1MHz$		_	800	pF				

Note 2. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\geq 2\%$ .

Note 3.  $f_T = |h_{FE}| \cdot f_{test}$ .



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